

1-Line Ultra Low Capacitance Bi-directional TVS Diode

Features

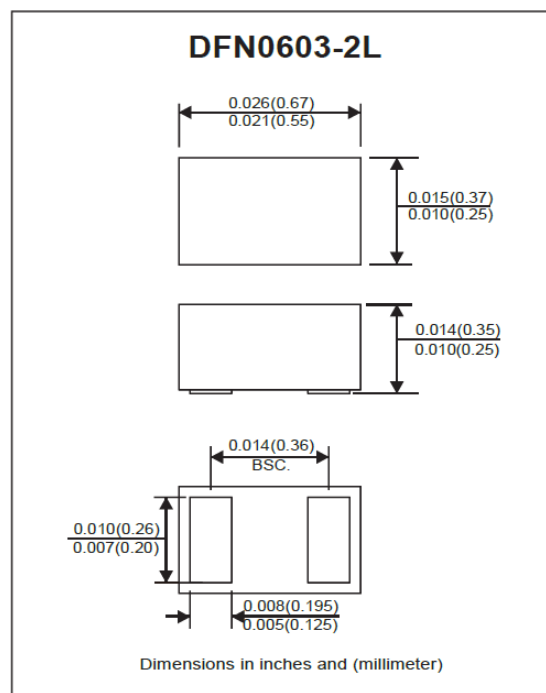
- IEC 61000-4-2 (ESD) $\pm 20\text{kV}$ (air), $\pm 20\text{kV}$ (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 9A (8/20 μs)
- Ultra low capacitance: 0.14pF typical
- Ultra small package: 0.6x0.3x0.3mm
- Operating voltage: 5V
- Low clamping voltage

Applications

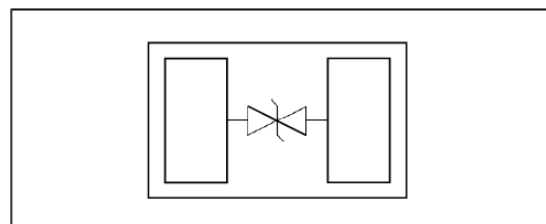
- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Mechanical Characteristics

- Package: DFN0603-2L (0.6x0.3x0.3mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Material: RoHS compliant



Circuit diagram

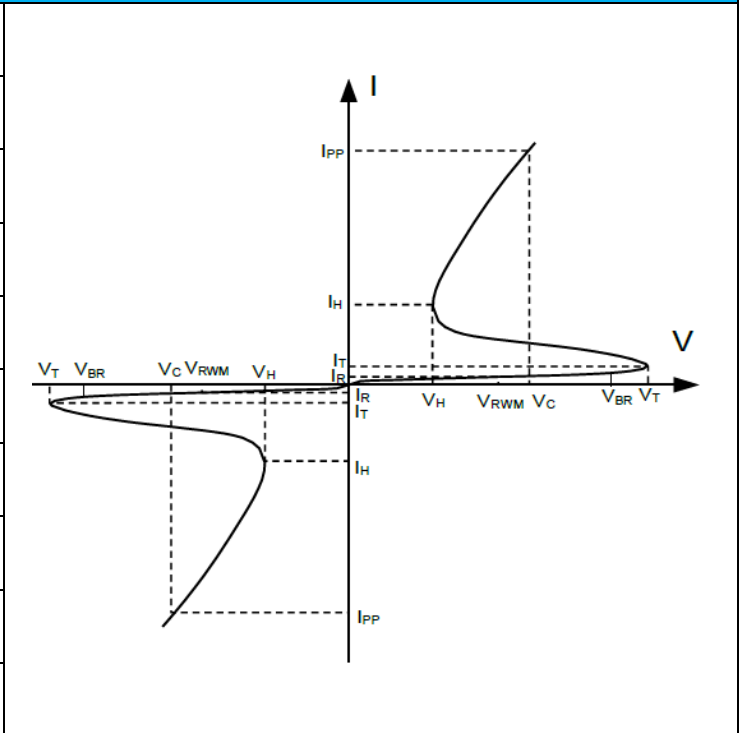


Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	50	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	9	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 20	KV
ESD per IEC 61000-4-2 (Contact)		± 20	KV
Operating Temperature Range	T_J	-55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to + 150	$^\circ\text{C}$

Electrical Parameters (T_A = 25°C Unless otherwise noted)

Symbol	Parameter
I _{PP}	Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Reverse Stand-Off Voltage
I _R	Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
V _T	Trigger Voltage
I _T	Test Current
V _H	Holding Voltage
I _H	Holding Current



Electrical Characteristics (T_A = 25°C Unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Reverse Working Voltage	V _{RWM}			5.0	5.5	V
Reverse breakdown Voltage	V _{BR}	I _T = 1mA	6.0			V
Reverse leakage current	I _R	V _{RWM} = 5.5V			0.01	μA
Clamping Voltage	V _C	I _{PP} = 1A, t _p = 8/20μs		3.2	4.0	V
Clamping Voltage	V _C	I _{PP} = 9A, t _p = 8/20μs		5.5	8.0	V
ESD Clamping Voltage	V _C	I _{PP} = 8A , (TLP=0.2/100ns)		4.5		V
ESD Clamping Voltage	V _C	I _{PP} = 16A , (TLP=0.2/100ns)		6.5		V
Dynamic Resistance	R _{DYN}	TLP=0.2/100ns		0.23		Ω
Junction capacitance	C _J	V _R = 1.0V, f = 1MHz		0.14	0.18	pF
Junction capacitance	C _J	V _R = 1.0V, f = 1GHz		0.13		pF

Typical Performance Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

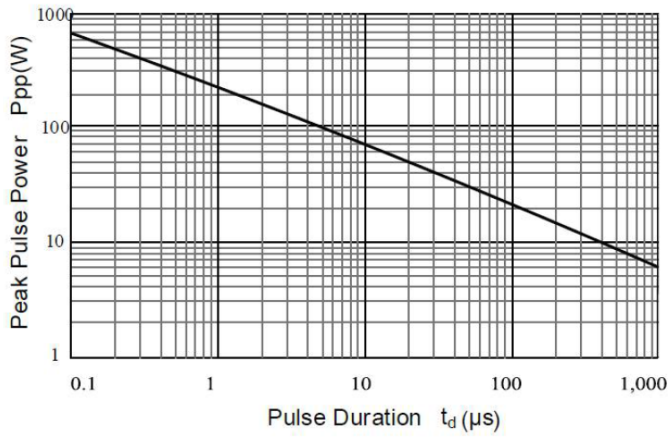


Fig 1. Peak Pulse Power vs. Pulse Time

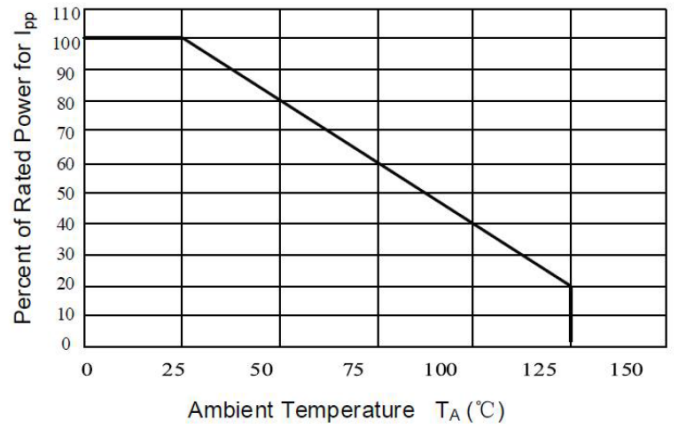


Fig 2. Power Derating Curve

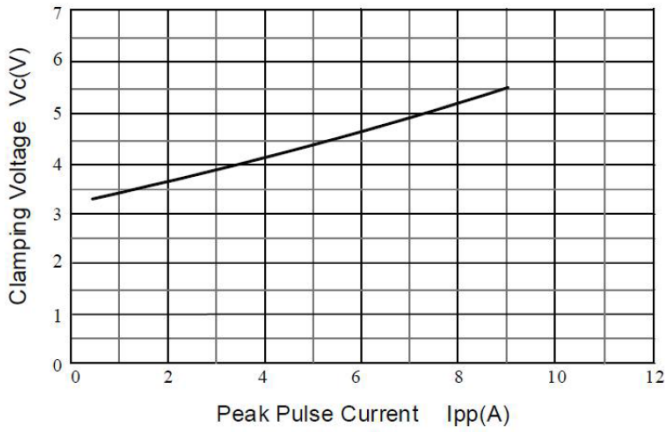


Fig 3. Clamping Voltage vs. Peak Pulse Current

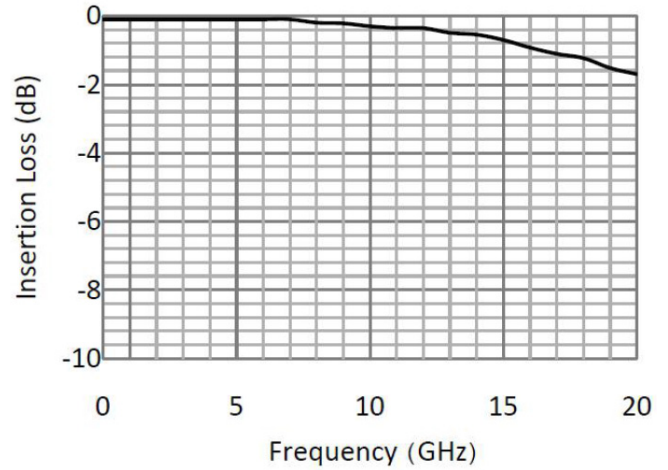


Fig 4. Insertion Loss S21

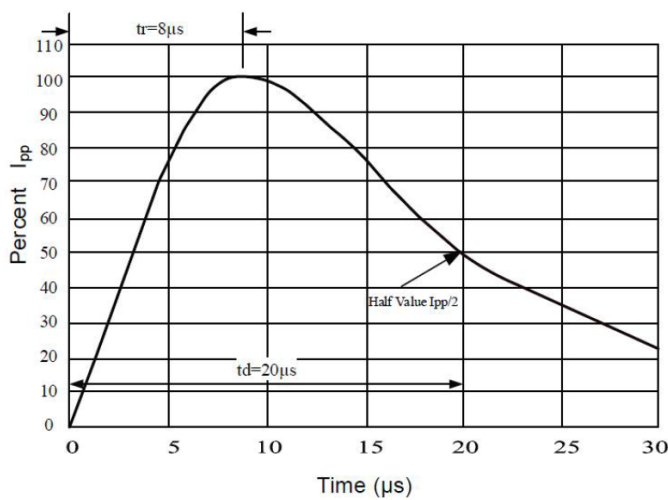


Fig 5. 8/20μs Pulse Waveform

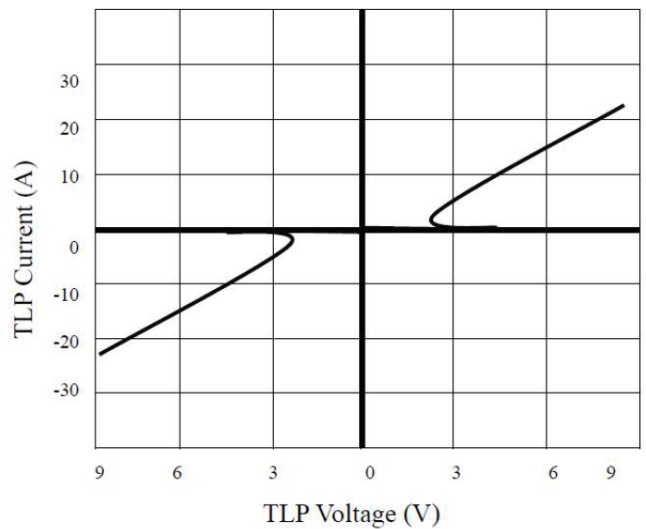
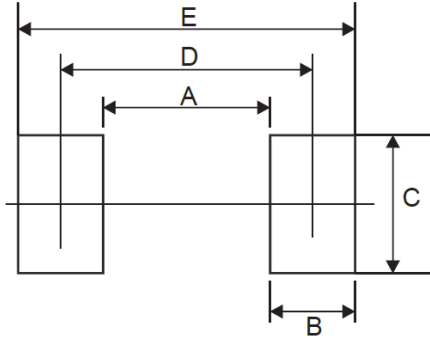


Fig 6. TLP I-V Curve


Suggested PAD Layout

Symbol	DFN0603-2L	
	(mm)	(inch)
A	0.16	0.006
B	0.24	0.009
C	0.34	0.013
D	0.40	0.016
E	0.64	0.025



The diagram illustrates the pad layout for the DFN0603-2L package. It shows two rectangular pads on a carrier tape. Dimension A is the distance between the centers of the two pads. Dimension B is the width of the right pad. Dimension C is the height of the right pad. Dimension D is the distance from the left edge of the left pad to the right edge of the right pad. Dimension E is the total width of the carrier tape, including the distance between the pads.

Marking Code

Part Number	Marking Code
STCD6050BSL	

Ordering information

Part Number	Package	Base qty	Reel Size	Delivery mode
		(pcs)	(inch)	
STCD6050BSL	DFN0603-2L	9,000	7	Tape and reel